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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Ji Ung Lee et al.			
					FILING DATE Filed Herewith	2/15/02	GROUP 2825 Filed Herewith	
U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Class	Subclas s	Filing Date If Appropriate	
NY	AA	5,482,870	01/09/96	Inoue				
	AB	5,372,973	12/13/94	Doan et al.				
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	AK							
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NY	AL	5-114734	05/07/93	Japan			Yes	No
	AM	3-194937	08/26/91	Japan			X	
	AN	3-155250	07/09/91	Japan			X	
	AO	A-2-143462	11/24/88	Japan			X	
NY	AP	61-252687	11/10/88	Japan			X	
	AQ	A-57-85262	11/17/80	Japan			X	
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
NY	AR	Polycrystalline Silicon Thin Film Transistor Incorporating a Semi-Insulating Field Plate for High Voltage Circuity on Glass,						
		F.J. Clough, E.M.S. Narayanan, Y. Chen, W. Eccleston, and W.J. Mone, Appl. Phys. Lett. 71 - 10/06/97, pages 2002-2004, 1997 American Institute of Physics.						
NY	AS	Geometry Dependence of the Transport Parameters in Field Effect Transistors Made From Amorphous Silicon, S. Grep, Mat. Res. Soc. Symp. Proc. 149,						
		pages 283-288, 1989 Materials Research Society.						
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EXAMINER	V. Yastrebov			DATE CONSIDERED		02/03/04		
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								